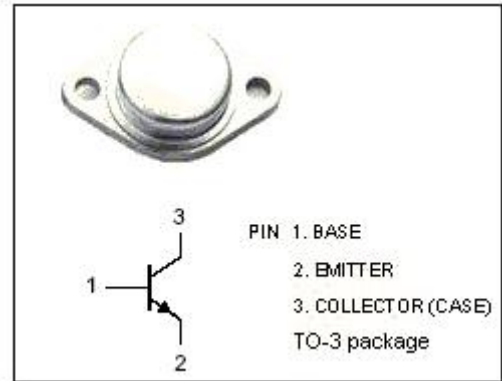


**isc Silicon NPN Power Transistor**
**2SC3462**
**DESCRIPTION**

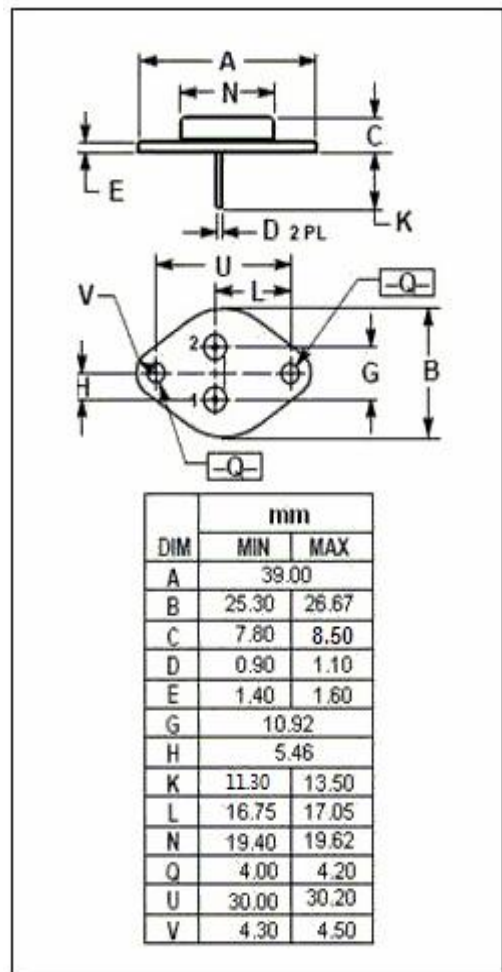
- High Breakdown Voltage-  
:  $V_{(BR)CBO} = 1100V(\text{Min})$
- Fast Switching Speed
- Wide Area of Safe Operation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for switching regulator Applications


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1100	V
$V_{CEO}$	Collector-Emitter Voltage	800	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	4.5	A
$I_{CM}$	Collector Current-Peak	15	A
$I_B$	Base Current-Continuous	2	A
$P_C$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	100	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



## isc Silicon NPN Power Transistor

## 2SC3462

## ELECTRICAL CHARACTERISTICS

T<sub>C</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 5mA; R <sub>BE</sub> = ∞	800			V
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 2A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.4A; L= 2mH; clamped	800			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	1100			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> =0			10	μA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.3A; V <sub>CE</sub> = 5V	10		40	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 1.5A; V <sub>CE</sub> = 5V	8			
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> =1.0MHz		90		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.3A; V <sub>CE</sub> = 10V		15		MHz

## Switching times

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 3A , I <sub>B1</sub> = 0.6A; I <sub>B2</sub> = -1.2A R <sub>L</sub> = 133 Ω ; V <sub>CC</sub> =400V			0.5	μs
t <sub>stg</sub>	Storage Time				3.0	μs
t <sub>f</sub>	Fall Time				0.3	μs

◆ h<sub>FE-1</sub> Classifications

K	L	M
10-20	15-30	20-40

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